



Vishay Semiconductors

Insulated Ultrafast Rectifier Module, 200 A



PRODUCT SUMMARY					
V_{R}	600 V				
$I_{F(AV)}$ per module at $T_C = 92$ °C	200 A				
t _{rr}	83 ns				

FEATURES

- Two fully independent diodes
- · Ceramic fully insulated package $(V_{ISOL} = 2500 V_{AC})$
- Ultrafast reverse recovery
- Ultrasoft reverse recovery current shape
- · Low forward voltage
- Optimized for power conversion: welding and industrial SMPS applications
- Industry standard outline
- Plug-in compatible with other SOT-227 packages
- · Easy to assemble
- · Direct mounting to heatsink
- UL approved file E78996



- Compliant to RoHS directive 2002/95/EC
- · Designed and qualified for industrial level

DESCRIPTION

The UFB200FA60P insulated modules integrate two state of the art Vishay Semiconductors ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The planar structure of the diodes, and the platinum doping life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness, and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be a predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, and DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_{R}		600	V	
Continuous forward current per diode	I _F	T _C = 85 °C	126	۸	
Single pulse forward current per diode	I _{FSM}	T _C = 25 °C	1000	Α	
Maximum power dissipation per module	P_{D}	T _C = 85 °C	360	W	
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V	
Operating junction and storage temperatures	T _J , T _{Stg}		- 55 to 175	°C	

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA		600	-	-	
F	V _{FM}	I _F = 100 A		- 1.46		1.78]
		I _F = 200 A		-	1.7	2.05	V
Forward voltage		I _F = 100 A	- T _J = 125 °C	-	1.23	1.52	
		I _F = 200 A		-	1.5	1.78	
Decreased as least a summer		$V_R = V_R$ rated		-	0.1	100	μA
Reverse leakage current I _{RM}		$T_J = 175 ^{\circ}\text{C}, V_R = V_R \text{rated}$		-	0.3	1.0	mA
Junction capacitance	C _T	V _R = 600 V		-	80	-	pF

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
B	t _{rr} ·	T _J = 25 °C	$I_F = 50 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	83	108	- ns
Reverse recovery time		T _J = 125 °C		-	182	235	
Dool, was a summer t		T _J = 25 °C		-	7	10	Α
Peak recovery current	I _{RRM}	T _J = 125 °C		-	18	22	
Reverse recovery charge Q	0	T _J = 25 °C		-	290	540	nC
	Q _{rr}	T _J = 125 °C		-	1595	2585	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	- R _{thJC}		-	-	0.5	
Junction to case, both leg conducting			-	-	0.25	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	1.3	-	N·m



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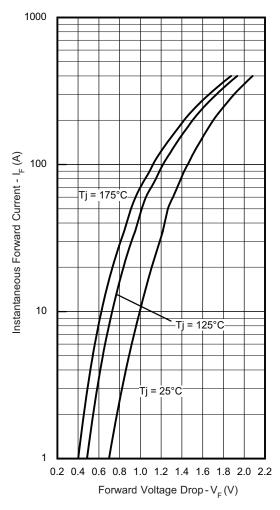


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Diode)

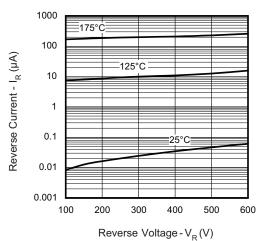


Fig. 2 - Typical Values of Reverse Current vs.
Reverse Voltage

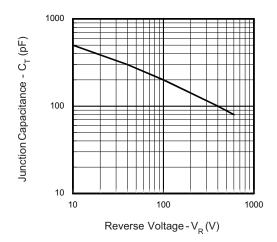


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

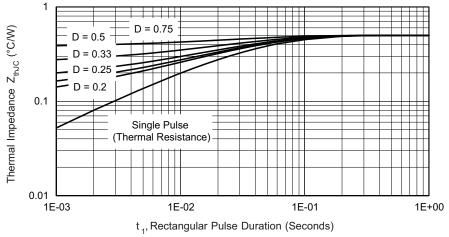


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Diode)

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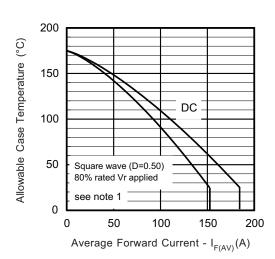


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

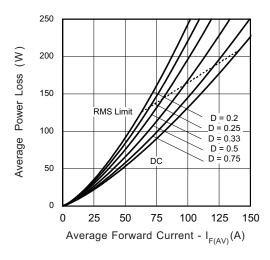


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

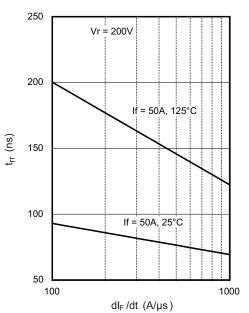


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

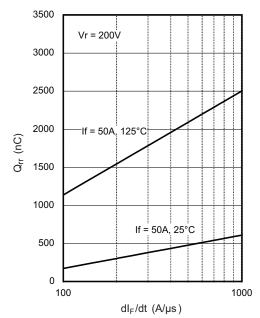


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC};$ $Pd = Forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R$ (1 - D); I_R at $V_{R1} = 80~\%$ rated V_R

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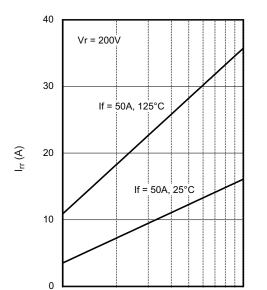


Fig. 9 - Typical Stored Current vs. dl_F/dt

 $dI_F/dt (A/\mu s)$

1000

100

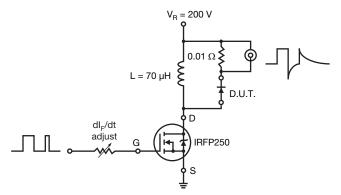
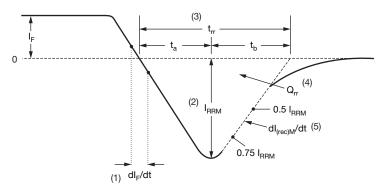


Fig. 10 - Reverse Recovery Parameter Test Circuit

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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) ${\rm Q_{rr}}$ area under curve defined by ${\rm t_{rr}}$ and ${\rm I_{RBM}}$

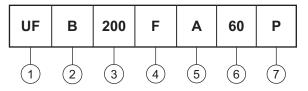
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

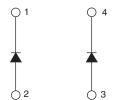
ORDERING INFORMATION TABLE

Device code



- Ultrafast rectifier
- 2 Ultrafast Pt diffused
- 3 Current rating (200 = 200 A)
- 4 Circuit configuration (2 separate diodes, parallel pin-out)
- 5 Package indicator (SOT-227 standard isolated base)
- 6 Voltage rating (60 = 600 V)
- 7 P = Lead (Pb)-free

CIRCUIT CONFIGURATION



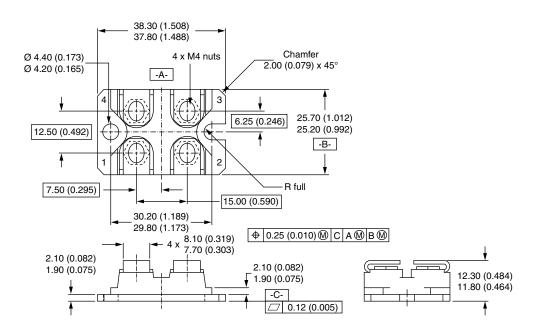
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95036</u>					
Packaging information	www.vishay.com/doc?95037				



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SOT-227

DIMENSIONS in millimeters (inches)



Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- · Controlling dimension: millimeter

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